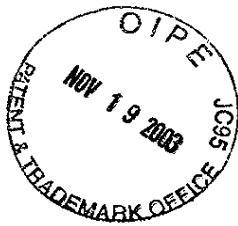


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MEMC 98-1451/2554.1
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster et al.

Art Unit 1775

Serial No. 10/073,506

Filed February 11, 2002

Confirmation No. 6190

For **THERMAL ANNEALING PROCESS FOR PRODUCING LOW DEFECT
DENSITY SINGLE CRYSTAL SILICON**

Examiner Matthew A. Anderson

November 19, 2003

AMENDMENT C

TO THE COMMISSIONER FOR PATENTS,

SIR:

This amendment is in response to the Office action mailed August 19, 2003.

Amendments to the Claims are reflected in the listing of claims which begins on page 2.

Remarks begin on page 12.

